

<b>Notice of References Cited</b>	Application/Control No. 10/803,342		Applicant(s)/Patent Under Reexamination KOEMTZOPOULOS ET AL.	
	Examiner Anita K. Alanko		Art Unit 1792	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-6,451,647	09-2002	Yang et al.	438/240
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
*	N	EP 200951 A2	11-1986	European Patent	CHEN et al.	
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#### NON-PATENT DOCUMENTS

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*	U	Vallon, S. et al "Polysilicon-germanium gate patterning studies in a high density plasma helicon source" JVST A 15(4) 1874-80, July 1997.
*	V	Kim, S.-J. et al "Notch- and Foot-Free Dual Polysilicon Gate Etch" Electrochem. Soc. Proc. Vol. 99-9, 361-5, 1999 (no month available).
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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